



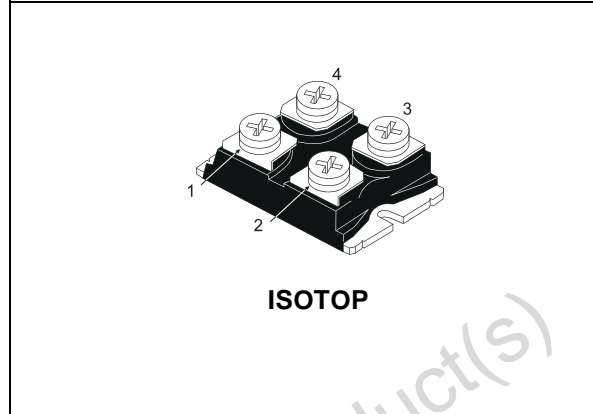
STGE50NB60HD

N-CHANNEL 50A - 600V - ISOTOP

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _C
STGY50NB60HD	600 V	< 2.8 V	50 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{CE(sat)})
- OFF LOSSES INCLUDE TAIL CURRENT
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- CO-PACKAGED WITH TURBOSWITCH™ ANTIPARALLEL DIODE



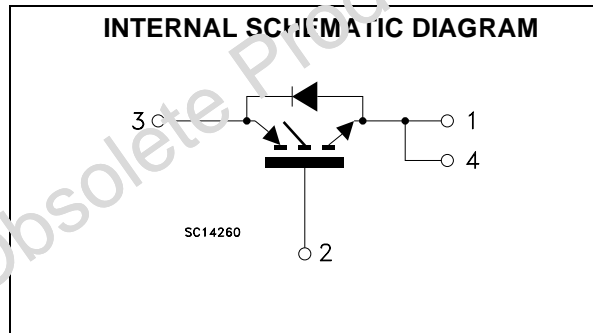
DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances.

The suffix "H" identifies a family optimized for high frequency applications (up to 120kHz) in order to achieve very high switching performances (reduced t_{fall}) maintaining a low voltage drop.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _C = 25°C	100	A
I _C	Collector Current (continuous) at T _C = 100°C	50	A
I _{CM} (■)	Collector Current (pulsed)	400	A
P _{TOT}	Total Dissipation at T _C = 25°C	300	W
	Derating Factor	2.4	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(■) PULSE WIDTH LIMITED BY SAFE OPERATING AREA

STGE50NB60HD

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.416	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
Rthc-h	Thermal Resistance Case-heatsink Typ	0.1	°C/W

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collectro-Emitter Breakdown Voltage	$I_C = 250 \mu A, V_{GE} = 0$	600			V
I_{CES}	Collector cut-off ($V_{GE} = 0$)	$V_{CE} = \text{Max Rating}, T_C = 25 \text{ }^\circ\text{C}$ $V_{CE} = \text{Max Rating}, T_C = 125 \text{ }^\circ\text{C}$			250 1000	μA μA
I_{GES}	Gate-Emitter Leakage Current ($V_{CE} = 0$)	$V_{GE} = \pm 20V, V_{CE} = 0$			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE} = V_{GE}, I_C = 250\mu A$	3		5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE} = 15V, I_C = 50 A$ $V_{GE} = 15V, I_C = 50 A, T_J = 125^\circ C$		2.3 1.9	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	$V_{CE} = 25 V, I_C = 50 A$		22		S
C_{ies}	Input Capacitance	$V_{CE} = 25V, f = 1 \text{ MHz}, V_{GE} = 0$		4500		pF
C_{oes}	Output Capacitance			450		pF
C_{res}	Reverse Transfer Capacitance			90		pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480V, I_C = 50 A,$ $V_{GE} = 15V$		260 28 15		nC nC nC
I_{CL}	Latching Current	$V_{clamp} = 480 V$ $T_J = 150^\circ C, R_G = 10 \Omega$	200			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 480 V, I_C = 50 A$ $R_G = 10\Omega, V_{GE} = 15 V$		20		ns
t_r	Rise Time			70		ns
$(di/dt)_{on}$ E_{on}	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480 V, I_C = 50 A,$ $R_G = 10\Omega, V_{GE} = 15 V,$ $T_J = 125^\circ C$		350 950		A/ μs μJ

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING OFF**

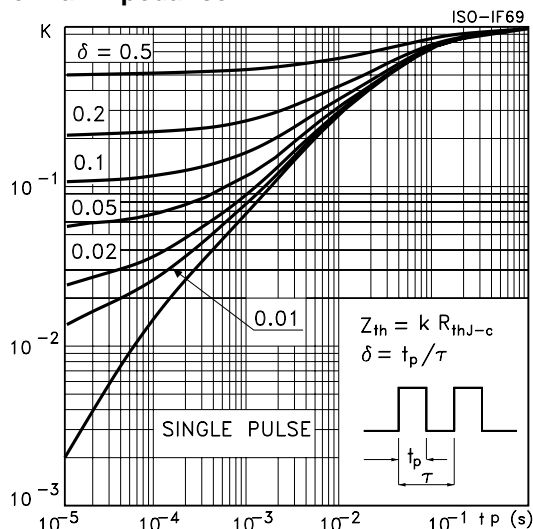
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-over Time	$V_{CC} = 480 \text{ V}$, $I_C = 50 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$		166		ns
$t_r(V_{off})$	Off Voltage Rise Time			48		ns
$t_{d(off)}$	Delay Time			326		ns
t_f	Fall Time			90		ns
$E_{off(**)}$	Turn-off Switching Loss			2.1		mJ
E_{ts}	Total Switching Loss			3		mJ
t_c	Cross-over Time	$V_{CC} = 480 \text{ V}$, $I_C = 50 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$ $T_j = 125 \text{ }^\circ\text{C}$		270		ns
$t_r(V_{off})$	Off Voltage Rise Time			75		ns
$t_{d(off)}$	Delay Time			340		ns
t_f	Fall Time			200		ns
$E_{off(**)}$	Turn-off Switching Loss			2.9		mJ
E_{ts}	Total Switching Loss			3.85		mJ

COLLECTOR-EMITTER DIODE

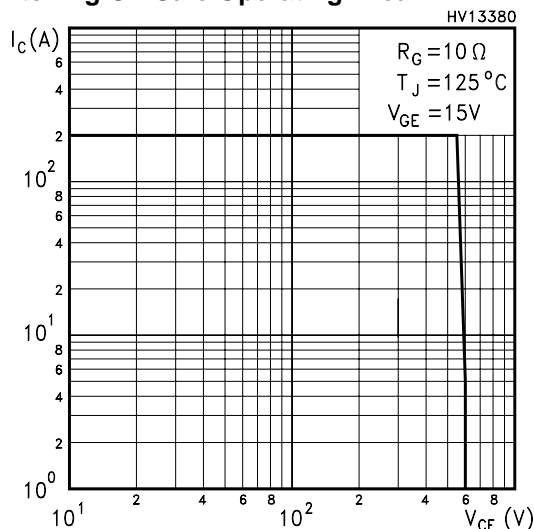
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f	Forward Current				50	A
I_{fm}	Forward Current pulsed				400	A
V_f	Forward On-Voltage	$I_f = 50 \text{ A}$ $I_f = 50 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$		1.65 2	2	V V
t_{rr}	Reverse Recovery Time	$I_f = 50 \text{ A}$, $V_R = 100 \text{ V}$, $T_j = 125 \text{ }^\circ\text{C}$, $di/dt = 100 \text{ A}/\mu\text{s}$		135		ns
Q_{rr}	Reverse Recovery Charge			500		nC
I_{rrm}	Reverse Recovery Current			7.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by max. junction temperature.
(**)Losses include Also the Tail (Jedec Standardization)

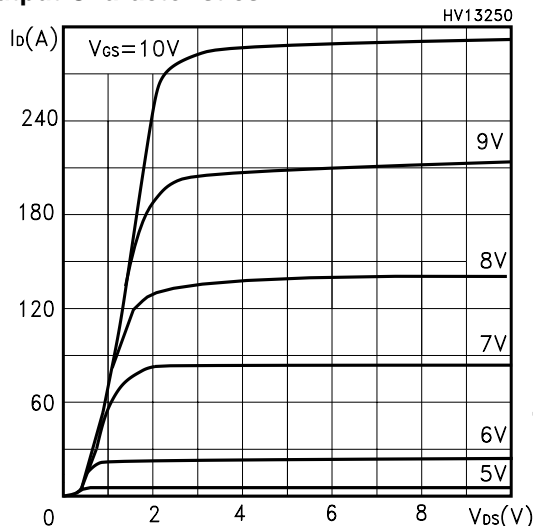
Thermal Impedance



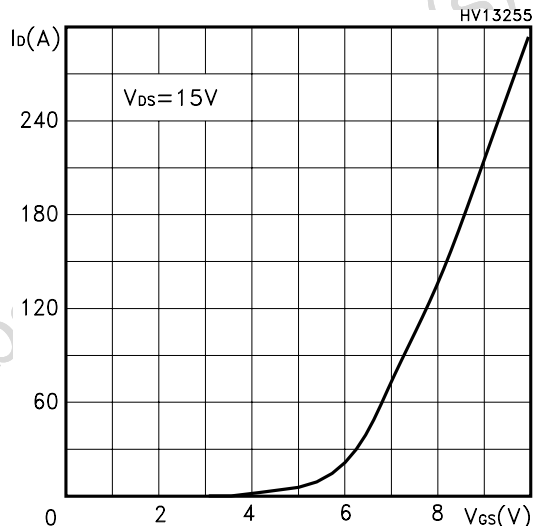
Switching Off Safe Operating Area



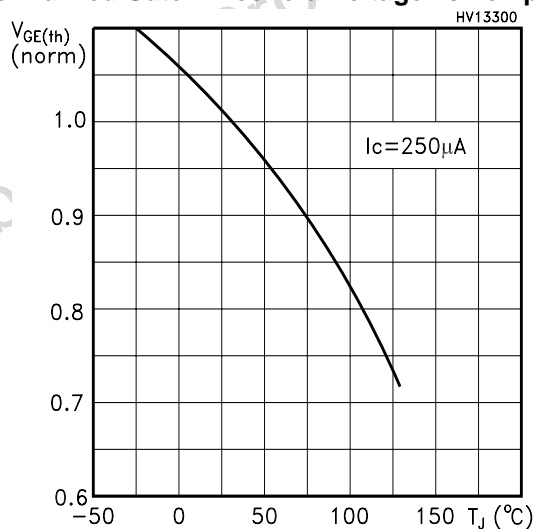
Output Characteristics



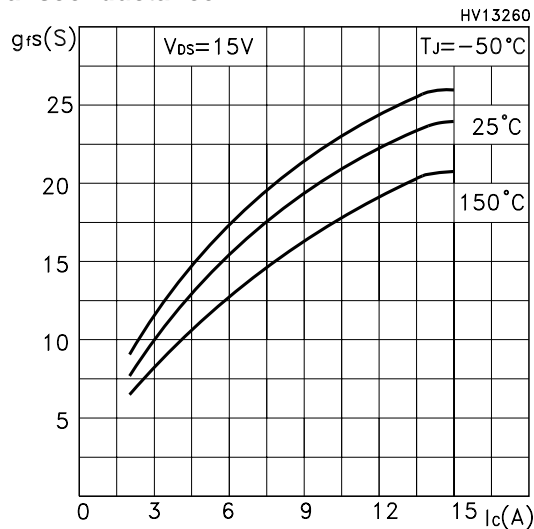
Transfer Characteristics



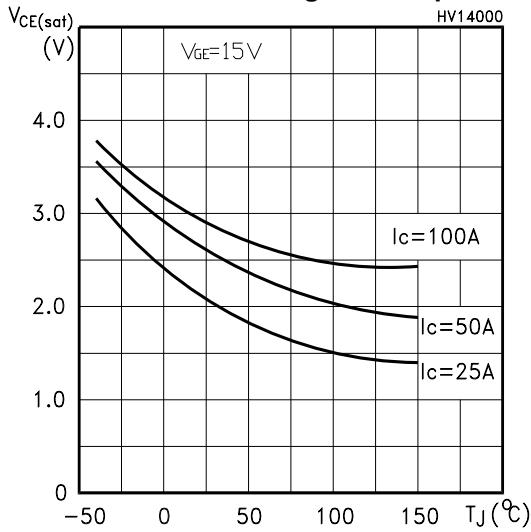
Normalized Gate Threshold Voltage vs Temp.



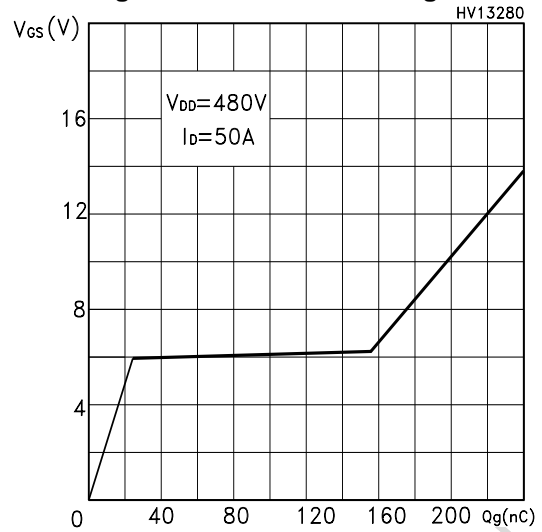
Transconductance



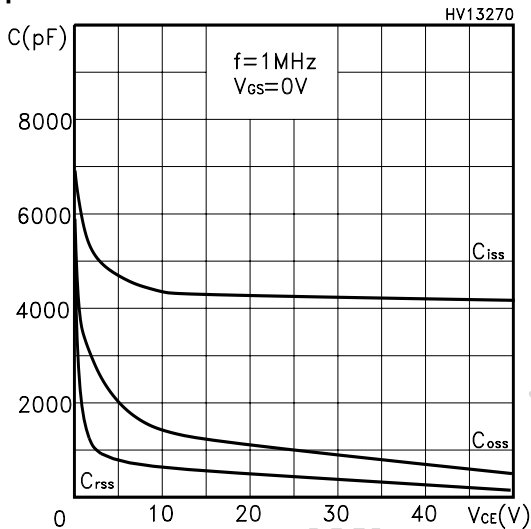
Collector-Emitter On Voltage vs Temperature



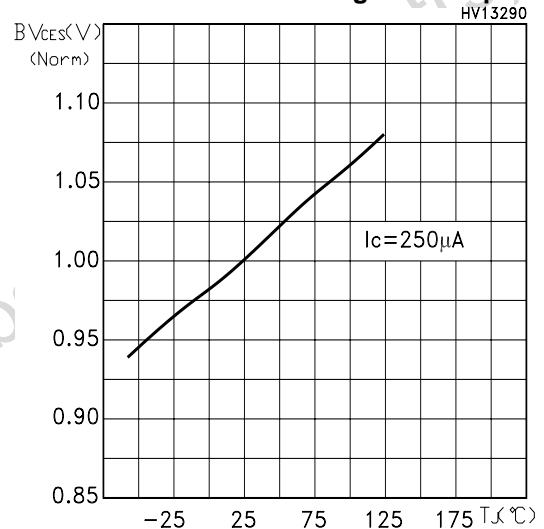
Gate-Charge vs Gate-Emitter Voltage



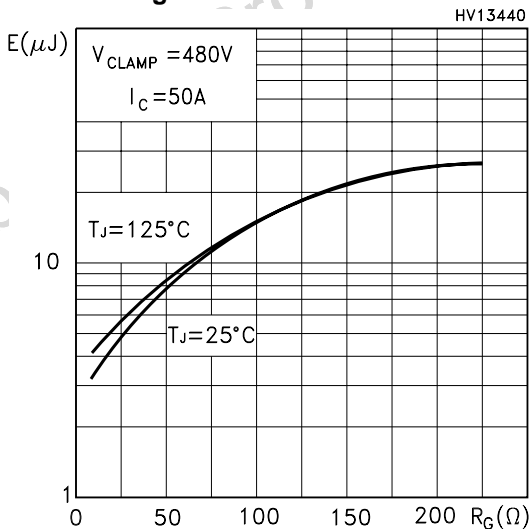
Capacitance Variations



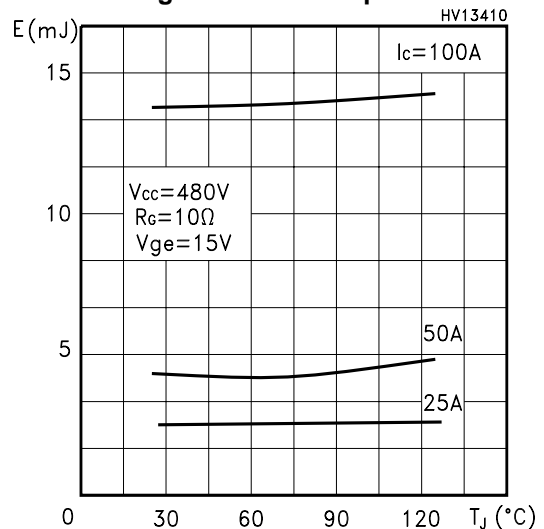
Normalized Break-down Voltage vs Temp.



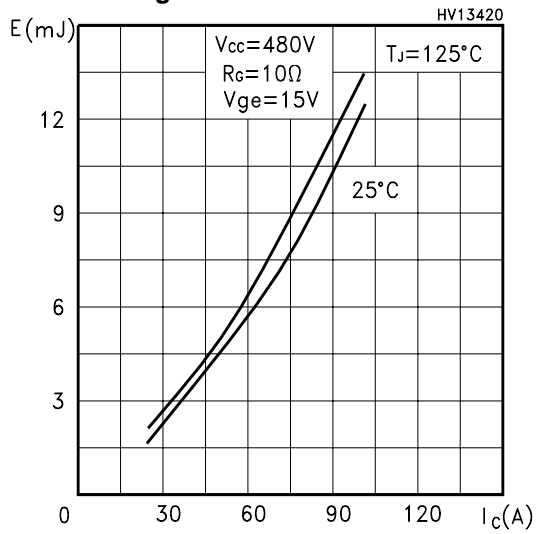
Total Switching losses vs Gate Resistance



Total Switching losses vs Temperature



Total Switching losses vs Ic



Diode Forward Voltage

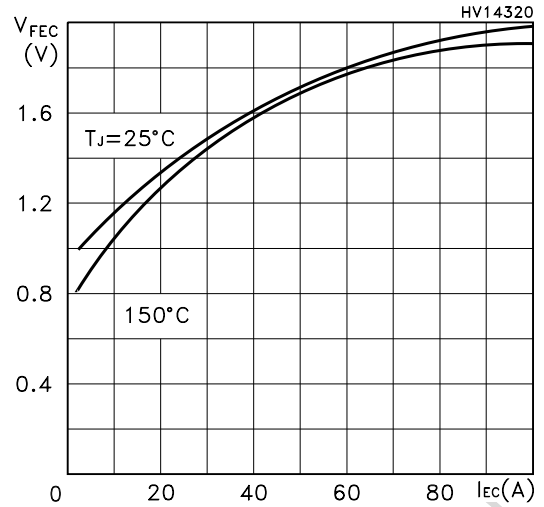


Fig. 1: Gate Charge test Circuit

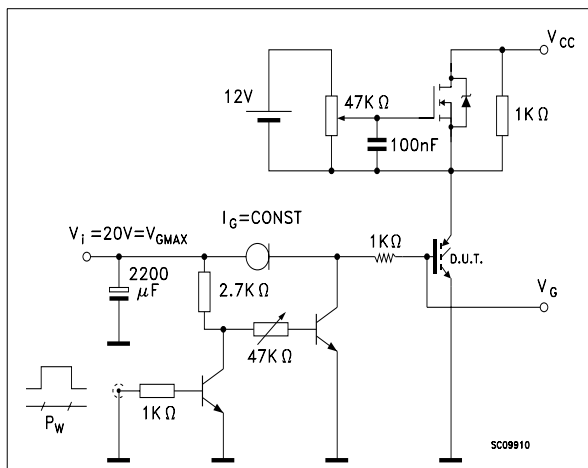
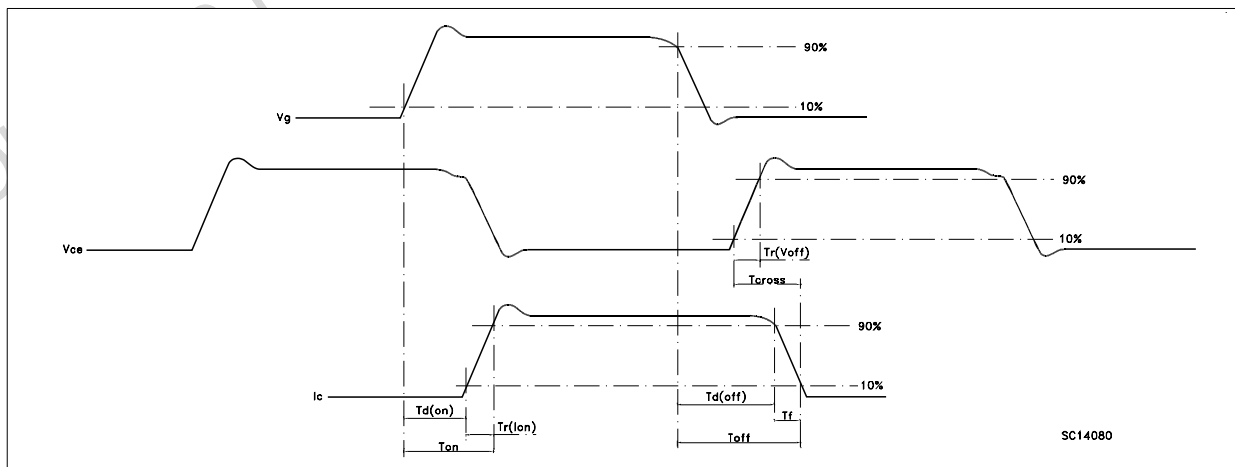
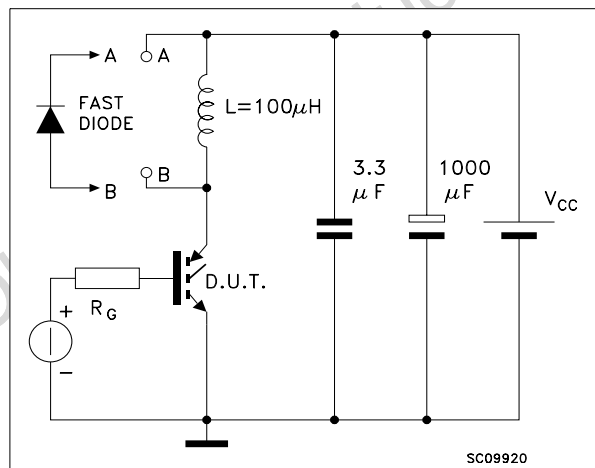
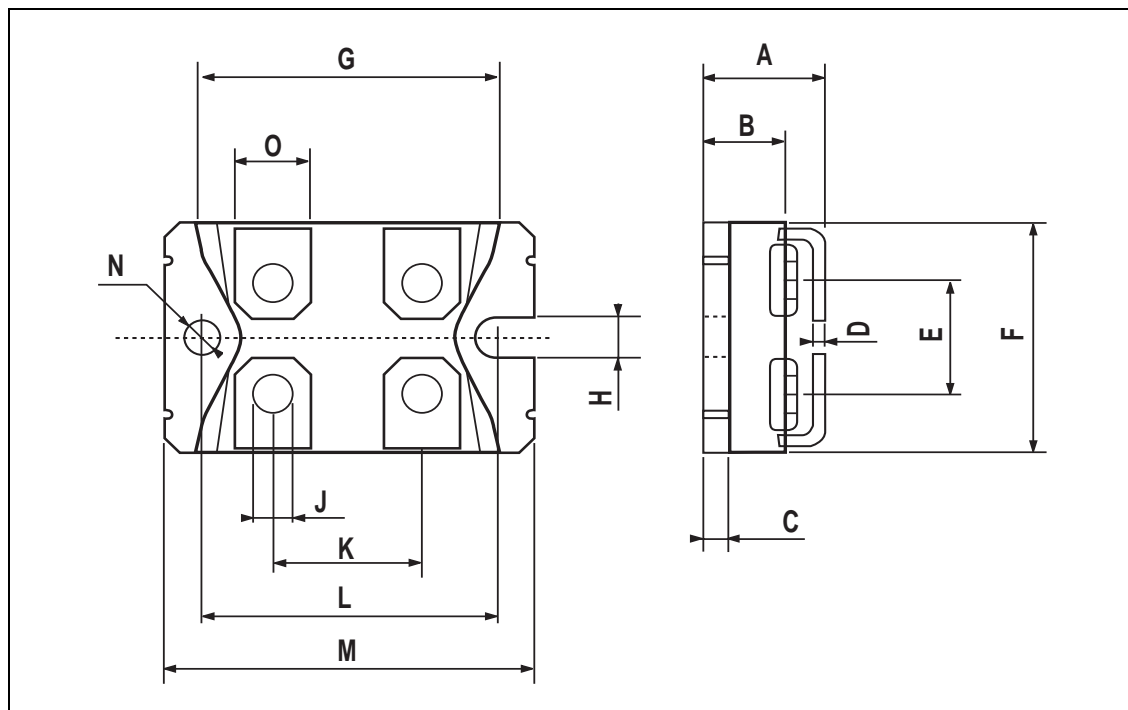


Fig. 2: Test Circuit For Inductive Load Switching



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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